SCES352C – JUNE 2001 – REVISED SEPTEMBER 2001	

 Member of the Texas Instruments Widebus™ Family 	DGG OR DGV PACKAGE (TOP VIEW)	
 TI-OPC[™] Circuitry Limits Ringing on Unevenly Loaded Backplanes 	IMODE1 $\begin{bmatrix} 1 & 48 \\ 48 \end{bmatrix}$ IMODE0 AI1 $\begin{bmatrix} 2 & 47 \end{bmatrix}$ BIAS V _{CC}	
 OEC[™] Circuitry Improves Signal Integrity and Reduces Electromagnetic Interference 	AO1 [] 3 46] B1 GND [] 4 45] GND	
 Bidirectional Interface Between GTLP Signal Levels and LVTTL Logic Levels 	Al2 5 44 0EAB AO2 6 43 B2	
 Split LVTTL Port Provides a Feedback Path for Control and Diagnostics Monitoring 	V _{CC} [] 7 42 [] <u>ERC</u> AI3 [] 8 41 [] OEAB	
LVTTL Interfaces Are 5-V Tolerant	AO3 9 40 B3	
 High-Drive GTLP Open-Drain Outputs (100 mA) 	GND [] 10 39 [] GND AI4 [] 11 38 [] CLKAB/LEAB	
 LVTTL Outputs (-24 mA/24 mA) 	AO4 12 37 B4 AO5 13 36 B5	
 Variable Edge-Rate Control (ERC) Input 	AI5 [] 14 35 [] CLKBA/LEBA	
Selects GTLP Rise and Fall Times for	GND 115 34 GND	
Optimal Data-Transfer Rate and Signal	AO6 🚺 16 33 🗍 B6	
Integrity in Distributed Loads	AI6 🛛 17 32 🕽 OEBA	
 I_{off}, Power-Up 3-State, and BIAS V_{CC} 	V _{CC}	
Support Live Insertion	AO7 [] 19 30 [] B7	
 Distributed V_{CC} and GND Pins Minimize 		
High-Speed Switching Noise		
 Latch-Up Performance Exceeds 100 mA Per 		
JESD 78, Class II	AI8 23 26 V _{REF} OMODE0 24 25 OMODE1	
 ESD Protection Exceeds JESD 22 		

- ESD Protection Exceeds JESD 22

 2000-V Human-Body Model (A114-A)
 - 1000-V Charged-Device Model (C101)

description

The SN74GTLP2033 is a high-drive, 8-bit, three-wire registered transceiver that provides inverted LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. The device allows for transparent, latched, and flip-flop modes of data transfer with separate LVTTL input and LVTTL output pins, which provides a feedback path for control and diagnostics monitoring, the same functionality as the SN74FB2033. The device provides a high-speed interface between cards operating at LVTTL logic levels and a backplane operating at GTLP signal levels. High-speed (about three times faster than standard LVTTL or TTL) backplane operation is a direct result of GTLP's reduced output swing (<1 V), reduced input threshold levels, improved differential input, OEC[™] circuitry, and TI-OPC[™] circuitry. Improved GTLP OEC and TI-OPC circuits minimize bus-settling time and have been designed and tested using several backplane models. The high drive allows incident-wave switching in heavily loaded backplanes with equivalent load impedance down to 11 Ω.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

OEC, TI-OPC, and Widebus are trademarks of Texas Instruments

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



Copyright © 2001, Texas Instruments Incorporated

SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

description (continued)

GTLP is the Texas Instruments derivative of the Gunning Transceiver Logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLP2033 is given only at the preferred higher noise-margin GTLP, but the user has the flexibility of using this device at either GTL (V_{TT} = 1.2 V and V_{RFF} = 0.8 V) or GTLP (V_{TT} = 1.5 V and V_{RFF} = 1 V) signal levels. For information on using GTLP devices in FB+/BTL applications, refer to TI application reports, Texas Instruments GTLP Frequently Asked Questions, literature number SCEA019, and GTLP in BTL Applications, literature number SCEA017.

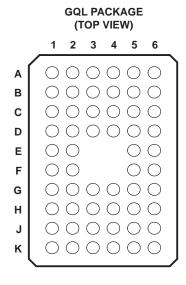
Normally, the B port operates at GTLP signal levels. The A-port and control inputs operate at LVTTL logic levels, but are 5-V tolerant and can be directly driven by TTL or 5-V CMOS devices. V_{RFF} is the B-port differential input reference voltage.

This device is fully specified for live-insertion applications using Ioff, power-up 3-state, and BIAS V_{CC}. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict. The BIAS V_{CC} circuitry precharges and preconditions the B-port input/output connections, preventing disturbance of active data on the backplane during card insertion or removal, and permits true live-insertion capability.

This GTLP device features TI-OPC circuitry, which actively limits overshoot caused by improperly terminated backplanes, unevenly distributed cards, or empty slots during low-to-high signal transitions. This improves signal integrity, which allows adequate noise margin to be maintained at higher frequencies.

High-drive GTLP backplane interface devices feature adjustable edge-rate control (ERC). Changing the ERC input voltage between low and high adjusts the B-port output rise and fall times. This allows the designer to optimize system data-transfer rate and signal integrity to the backplane load.

When V_{CC} is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, OEAB should be tied to V_{CC} through a pullup resistor and OEAB and OEBA should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sinking/current-sourcing capability of the driver.



terminal assignments

	1	2	3	4	5	6
Α	IMODE1	NC	NC	NC	NC	IMODE0
в	AO1	Al1	GND	GND	BIAS V _{CC}	B1
С	AO2	Al2	VCC	ERC	OEAB	B2
D	AO3	AI3	GND	GND	OEAB	B3
Е	AO4	Al4			CLKAB/LEAB	B4
F	AO5	AI5			CLKBA/LEBA	B5
G	AO6	Al6	GND	GND	OEBA	B6
н	AO7	AI7	VCC	VCC	LOOPBACK	B7
J	AO8	AI8	GND	GND	V _{REF}	B8
κ	OMODE0	NC	NC	NC	NC	OMODE1

NC = No internal connection



TA	PACKAGE [†]		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	TSSOP – DGG	Tape and reel	SN74GTLP2033DGGR	GTLP2033
	TVSOP – DGV	Tape and reel	SN74GTLP2033DGVR	GT2033
	VFBGA – GQL	Tape and reel	SN74GTLP2033GQLR	GR033

ORDERING INFORMATION

[†] Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

functional description

The SN74GTLP2033 is a high-drive (100 mA), 8-bit, three-wire registered transceiver containing D-type latches and D-type flip-flops for data-path operation in the transparent, latched, or flip-flop modes. Data transmission is complementary, with inverted AI data going to the B port and inverted B data going to AO. The split LVTTL AI and AO provides a feedback path for control and diagnostics monitoring.

The logic element for data flow in each direction is configured by two mode (IMODE1 and IMODE0 for B to A, OMODE1 and OMODE0 for A to B) inputs as a buffer, D-type flip-flop, or D-type latch. When configured in the buffer mode, the inverted input data appears at the output port. In the flip-flop mode, data is stored on the rising edge of the appropriate clock (CLKAB/LEAB or CLKBA/LEBA) input. In the latch mode, the clock inputs serve as active-high transparent latch enables.

Data flow in the B-to-A direction, regardless of the logic element selected, is further controlled by the LOOPBACK input. When LOOPBACK is low, B-port data is the B-to-A input. When LOOPBACK is high, the output of the selected A-to-B logic element (prior to inversion) is the B-to-A input.

The AO enable/disable control is provided by OEBA. When OEBA is low or when V_{CC} is less than 1.5 V, AO is in the high-impedance state. When OEBA is high, AO is active (high or low logic levels).

The B port is controlled by OEAB and OEAB. If OEAB is low, OEAB is high, or V_{CC} is less than 1.5 V, the B port is inactive. If OEAB is high and OEAB is low, the B port is active.

The A-to-B and B-to-A logic elements are active, regardless of the state of their associated outputs. The logic elements can enter new data (in flip-flop and latch modes) or retain previously stored data while the associated outputs are in the high-impedance (AO) or inactive (B port) states.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

INPUTS OUTPUT MODE OEBA OEAB OEAB OMODE1 OMODE0 IMODE1 IMODE0 LOOPBACK L L Х Х Х Х Х Х Ζ Isolation Х Х Х L Х Н Х Х Х н L L L Х Х Х Buffer Х Н L L Н Х Х Х Flip-flop Inverted AI to B Н Х Х Х Х Х Н L Latch Н Х Х L Х L L L Inverted B to AO Buffer Х Х Х L L L Н Н Х Н L Х Х L н L Inverted B to AO Flip-flop Н Х Н Х Х L Н L Х Х Н L Х Н Х L Inverted B to AO Latch Х Х Н Х L Н Х Н Х Н L Х Х L L Н AI to AO Buffer Н Х Н Х Х L L Н н L Х Х Х L н Н AI to AO Flip-flop Н Н н Х Н Х Х L Н L Х Х Х Н Х Н AI to AO Latch Н Х Н Х Х Н Х Н Inverted AI to B, Transparent with Н Х Х Н L Х Х L Inverted B to AO feedback path

FUNCTION/MODE

Function Tables

ENABLE/DISABLE

INPUTS		OUTI	PUTS	
OEBA	OEAB	OEAB	AO	В
L	Х	Х	Z	
Н	Х	Х	Active	
Х	L	L		Z
Х	L	Н		Z
Х	Н	L		Active
Х	Н	Н		Z

BUFFER

INPUT	OUTPUT
L	Н
Н	L

LATCH				
INPU				
CLK/LE DATA		OUTPUT		
Н	L	Н		
Н	н	L		
L	Х	Q ₀		



Function Tables (Continued)

LOOPBACK

LOOPBACK	Q†
L	B port
Н	Point P [‡]

 $^{\dagger}\,\text{Q}$ is the input to the B-to-A

logic element.

[‡] P is the output of the A-to-B logic element (see functional block diagram).

SELECT

INP	UTS	SELECTED LOGIC
MODE1	MODE0	ELEMENT
L	L	Buffer
L	Н	Flip-flop
н	Х	Latch



INPUTS		OUTPUT
CLK/LE	CLK/LE DATA	
L	Х	Q ₀
\uparrow	L	Н
\uparrow	Н	L

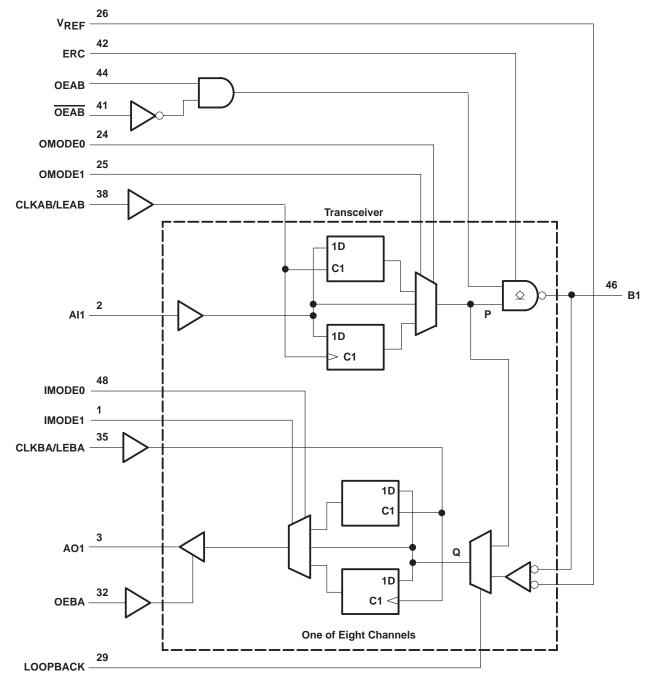
B-PORT EDGE-RATE CONTROL (ERC)

INPUT ERC	OUTPUT B-PORT
LOGIC LEVEL	EDGE RATE
Н	Slow
L	Fast



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

functional block diagram



Pin numbers shown are for the DGG and DGV packages.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage range, V _{CC} and BIAS V _{CC} Input voltage range, V _I (see Note 1): AI port, ERC, and control inputs B port and V _{REF}	\ldots –0.5 V to 7 V
Voltage range applied to any output in the high-impedance or power-off state, V _O (see Note 1): AO port	
Current into any output in the low state, I _O : AO portB port	48 mA
Current into any A-port output in the high state, I_O (see Note 2) Continuous current through each V_{CC} or GND Input clamp current, I_{IK} ($V_I < 0$) Output clamp current, I_{OK} ($V_O < 0$)	48 mA ±100 mA –50 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package DGV package GQL package Storage temperature range, T _{stg}	70°C/W 58°C/W 42°C/W

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

2. This current flows only when the output is in the high state and $V_O > V_{CC}$.

3. The package thermal impedance is calculated in accordance with JESD 51-7.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

recommended operating conditions (see Notes 4 through 7)

			MIN	NOM	MAX	UNIT
V _{CC} , BIAS V _{CC}	Supply voltage		3.15	3.3	3.45	V
	—	GTL	1.14	1.2	1.26	
VTT	Termination voltage	GTLP	1.35	1.5	1.65	V
	Defense en lle ne	GTL	0.74	0.8	0.87	
V _{REF}	Reference voltage	GTLP	0.87	1	1.1	V
	land on the ne	B port			VTT	v
VI	Input voltage	Except B port and VREF		VCC	5.5	V
	Litely lossed formation from a	B port	V _{REF} +0.05			
VIH	High-level input voltage	Except B port	2			V
		B port		,	V _{REF} -0.05	
VIL	Low-level input voltage	Except B port			0.8	V
IIK	Input clamp current				-18	mA
ЮН	High-level output current	AO			-24	mA
		AO			24	
IOL	Low-level output current	B port			100	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	Outputs enabled			10	ns/V
$\Delta t / \Delta V_{CC}$	Power-up ramp rate	20			μs/V	
T _A	Operating free-air temperature		-40		85	°C

NOTES: 4. All unused control and B-port inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

5. Proper connection sequence for use of the B-port I/O precharge feature is GND and BIAS V_{CC} = 3.3 V first, I/O second, and V_{CC} = 3.3 V last, because the BIAS V_{CC} precharge circuitry is disabled when any V_{CC} pin is connected. The control and V_{REF} inputs can be connected anytime, but normally are connected during the I/O stage. If B-port precharge is not required, any connection sequence is acceptable but, generally, GND is connected first.

6. VTT and RTT can be adjusted to accommodate backplane impedances if the dc recommended IOL ratings are not exceeded.

 V_{REF} can be adjusted to optimize noise margins, but normally is two-thirds V_{TT}. TI-OPC circuitry is enabled in the A-to-B direction and is activated when V_{TT} > 0.7 V above V_{REF}. If operated in the A-to-B direction, V_{REF} should be set to within 0.6 V of V_{TT} to minimize current drain.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

electrical characteristics over recommended operating free-air temperature range for GTLP (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT		
VIK		V _{CC} = 3.15 V,	lj = -18 mA			-1.2	V	
		V _{CC} = 3.15 V to 3.45 V,	I _{OH} = -100 μA	V _{CC} -0.2				
∨он	AO		I _{OH} = -12 mA	2.4			V	
		V _{CC} = 3.15 V	I _{OH} = -24 mA	2				
		$V_{CC} = 3.15 \text{ V to } 3.45 \text{ V},$	l _{OL} = 100 μA			0.2		
	AO	V _{CC} = 3.15 V	I _{OL} = 12 mA			0.4		
Vol		VCC = 3.13 V	I _{OL} = 24 mA			0.5	V	
VOL			I _{OL} = 10 mA			0.2	v	
	B port	V _{CC} = 3.15 V	I _{OL} = 64 mA			0.4		
			I _{OL} = 100 mA			0.55		
II‡	AI and control inputs	V _{CC} = 3.45 V,	VI = 0 or 5.5 V			±10	μA	
. +	AO	V _{CC} = 3.45 V,	$V_{O} = 0$ to 5.5 V			±10		
loz‡	B port	V_{CC} = 3.45 V, V_{REF} within 0.6 V of V_{TT} ,	$V_{O} = 0$ to 2.3 V			±10	μA	
		$V_{CC} = 3.45 \text{ V}, \text{ I}_{O} = 0,$	Outputs high			40		
ICC	AO or B port	V_I (A-port or control input) = V_{CC} or GND,	Outputs low	40		40	mA	
		V_{I} (B port) = V_{TT} or GND	Outputs disabled			40	1	
ΔICC§		V_{CC} = 3.45 V, One AI or control input at V_{CC} Other AI or control inputs at V_{CC} or GND	V_{CC} = 3.45 V, One AI or control input at V_{CC} – 0.6 V, Other AI or control inputs at V_{CC} or GND				mA	
~	AI						- 5	
Ci	Control inputs	$V_{l} = 3.15 \text{ V or } 0$		3.5	5.5	pF		
Co	AO	V _O = 3.15 V or 0		5	6	pF		
Cio	B port	V _O = 1.5 V or 0		8.5	10	pF		

[†] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

 \ddagger For I/O ports, the parameter I_{OZ} includes the input leakage current.

§ This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

hot-insertion specifications for A port over recommended operating free-air temperature range

PARAMETER		TEST CONDITIONS						
l _{off}	$V_{CC} = 0,$	$V_{I} \text{ or } V_{O} = 0 \text{ to } 5.5 \text{ V}$			10	μΑ		
IOZPU	$V_{CC} = 0$ to 1.5 V,	V_{O} = 0.5 V to 3 V,	$OEBA = V_{CC}$		±30	μΑ		
IOZPD	V _{CC} = 1.5 V to 0,	V_{O} = 0.5 V to 3 V,	$OEBA = V_{CC}$		±30	μΑ		

live-insertion specifications for B port over recommended operating free-air temperature range

PARAMETER		TEST CONDITION	IS	MIN	MAX	UNIT					
loff	$V_{CC} = 0,$	BIAS $V_{CC} = 0$,	V_{I} or $V_{O} = 0$ to 1.5 V		10	μA					
IOZPU	V_{CC} = 0 to 1.5 V, BIAS V	C = 0 to 1.5 V, BIAS V _{CC} = 0, V _O = 0.5 V to 1.5 V, $\overline{\text{OEAB}}$ = 0 and OEAB = V _{CC}									
IOZPD	V_{CC} = 1.5 V to 0, BIAS V	$_{\rm C}$ = 1.5 V to 0, BIAS V _{CC} = 0, V _O = 0.5 V to 1.5 V, $\overline{\rm OEAB}$ = 0 and OEAB = V _{CC}									
ICC	V _{CC} = 0 to 3.15 V				5	mA					
(BIAS V _{CC})	V _{CC} = 3.15 V to 3.45 V	BIAS V_{CC} = 3.15 V to 3.45 V,		10	μA						
VO	$V_{CC} = 0,$	BIAS V_{CC} = 3.3 V,	IO = 0	0.95	1.05	V					
IO	$V_{CC} = 0,$	BIAS V _{CC} = 3.15 V to 3.45 V,	$V_O (B \text{ port}) = 0.6 \text{ V}$	-1		μA					



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (unless otherwise noted)

			MIN	MAX	UNIT
fclock	Clock frequency			175	MHz
tw	Pulse duration	CLKAB/LEAB or CLKBA/LEBA	2.8		ns
		AI before CLKAB↑	1.1		
t _{su} Setup time		AI before CLKBA [↑]	1.4		
		B before CLKBA↑	1		
	Setup time	AI before LEAB↓	1.6		ns
	Al before LEBA↓		2.1		
		B before LEBA↓	2.2		
		AI after CLKAB↑	0.3		
		AI after CLKBA↑	0.2		
		B after CLKBA↑	0.6		
t _h Hold time	Hold time	AI after LEAB↓	0.3		ns
		AI after LEBA↓	0		
		B after LEBA↓	0		



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE [†]	MIN TYP	¢ MAX	UN
f _{max}				175		MH
^t PLH	AI	_		3	7.4	
^t PHL	(buffer)	В	Slow	3	7.1	ns
^t PLH	AI	5	.	2	5.9	
^t PHL	(buffer)	В	Fast	2	5.8	ns
^t PLH	В	10		1	5.7	
^t PHL	(buffer)	AO	-	1	5	ns
^t PLH	LEAB	В	Clow	4.2	8.6	
^t PHL	(latch mode)	D	Slow	3.2	7.7	n
^t PLH	LEAB	P	Foot	3.2	7.6	
^t PHL	(latch mode)	В	Fast	2.8	6.7	n
^t PLH	LEAB	40		2	7	
^t PHL	(latch mode)	AO	-	1.8	6.3	n
^t PLH	LEBA	AO		1	5.7	_
^t PHL	(latch mode)	AU	-	1	4.7	n
^t PLH		5	01	3.8	7.5	
^t PHL	OEAB	В	Slow	3.1	7	n
^t PLH	OEAB	P	Fast	2.5	6	
^t PHL	UEAD	В	Fast	2.5	6	n
^t PLH	OEAB	P	Claur	3.5	7.5	
^t PHL	OEAB	В	Slow	3	7.2	ns
^t PLH	0545	5	Fast	2.5	6	
^t PHL	OEAB	В	Fast	2.5	6	n
^t PZH	0554	40		1	4.7	
^t PZL	OEBA	AO	-	1	3.4	n
^t PHZ	0554	40		1	5.2	
^t PLZ	OEBA	AO	-	1	4.9	n
^t PLH	CLKAB	5	01	4.4	8.8	
^t PHL	(flip-flop mode)	В	Slow	3.6	8.1	n
^t PLH	CLKAB	5	Fast	3.2	7.2	
^t PHL	(flip-flop mode)	В	Fast	3.1	6.9	n
^t PLH	CLKAB	10		2	6.9	
^t PHL	(flip-flop mode)	AO	-	1.8	6.4	n
^t PLH	CLKBA	10		1	5.6	
^t PHL	(flip-flop mode)	AO	-	1	4.9	n
^t PLH	OMODE		Class	3.8	8.7	_
^t PHL	UNUDE	В	Slow	3.2	8.2	n
^t PLH	OMODE		E	2.7	7.2	
^t PHL	OMODE	В	Fast	2.7	7.2	n
^t PLH	IMODE	AO		1	5.6	~
^t PHL	IWODE	AU	-	1	4.6	n

[†]Slow (ERC = H) and Fast (ERC = L)

[‡] All typical values are at V_{CC} = 3.3 V, $T_A = 25^{\circ}C$.



SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 1) (continued)

PARAMETER	FROM (INPUT)			MIN	TYP‡	MAX	UNIT
^t PLH				2.5	6.2	6.2	
^t PHL	LOOPBACK	AO	-	2	5	5	ns
^t PLH	AI	10		1	5.6	5.6	
^t PHL	(loopback high)	AO	-	1	5	5	ns
		Rise time, B-port outputs (20% to 80%)					
tr	Rise time, B-port outputs (2	.0% to 80%)	Fast	Fast			ns
	Rise time, AO (10% to 90%)			3.5		
		Fall time, \overline{B} -port outputs (80% to 20%)			Slow 3		
t _f	Fail time, B-port outputs (80				Fast 1.8		
	Fall time, AO (90% to 10%)	Fall time, AO (90% to 10%)					

[†]Slow (ERC = H) and Fast (ERC = L)

[‡] All typical values are at V_{CC} = 3.3 V, T_A = 25° C.

skew characteristics over recommended ranges of supply voltage and operating free-air temperature (see Figure 1)§

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE [†]	MIN TYP‡	МАХ	UNIT	
^t sk(LH) [¶]	AI	В	Slow	0.5	1		
^t sk(HL) [¶]	AI	В	510W	0.5	1	ns	
^t sk(LH) [¶]	AI	В	Fast	0.4	0.9		
^t sk(HL) [¶]	AI	В	Fasi	0.4	0.9	ns	
^t sk(LH) [¶]	CLKAB/LEAB	В	Slow	0.5	1	ns	
^t sk(HL) [¶]	CLKAD/LEAD	В	510W	0.5	1	115	
^t sk(LH) [¶]	CLKAB/LEAB	В	Fast	0.4	0.9		
^t sk(HL) [¶]	CLKAD/LEAD	В	Fasi	0.4	0.9	ns	
	AI	В	Slow	1.4	2		
+ 1 / ···¶	A	В	Fast	0.6 1.4			
tsk(t)¶	CLKAB/LEAB	В	Slow	1.8	2.5	ns	
	ULIVAD/LEAD		Fast	0.9	1.8		

[†]Slow (ERC = L) and Fast (ERC = H)

[‡] All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

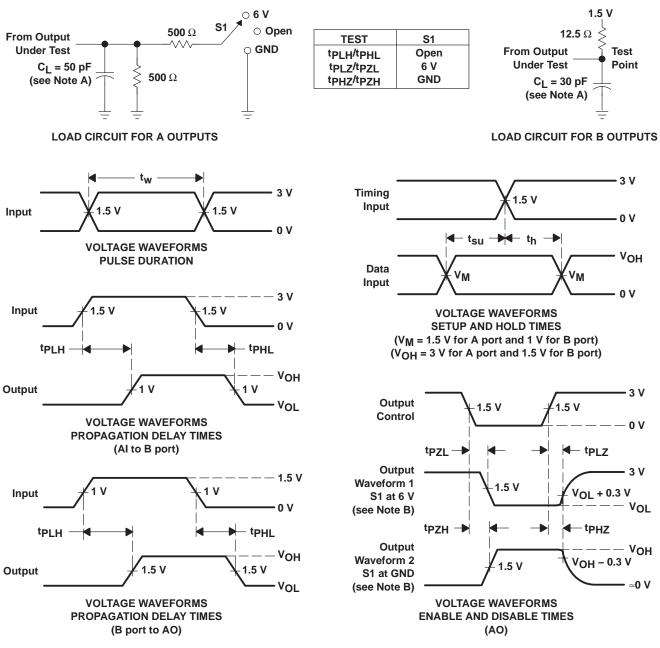
§ Actual skew values between the GTLP outputs could vary on the backplane due to the loading and impedance seen by the device.

Itsk(LH)/tsk(HL) and tsk(t) – Output-to-output skew is defined as the absolute value of the difference between the actual propagation delay for all outputs with the same packaged device. The specifications are given for specific worst-case V_{CC} and temperature and apply to any outputs switching in the same direction either high to low [t_{sk(HL)}] or low to high [t_{sk(LH)}] or in opposite directions, both low to high and high to low [t_{sk(t)}].



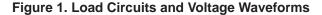
SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

PARAMETER MEASUREMENT INFORMATION



- NOTES: A. CL includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \approx 10 MHz, Z_O = 50 Ω , t_f \approx 2 ns, t_f \approx 2 ns.

D. The outputs are measured one at a time with one transition per measurement.





SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The preceding switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 1). However, the designer's backplane application is probably a distributed load. The physical representation is shown in Figure 2. This backplane, or distributed load, can be approximated closely to a resistor inductance capacitance (RLC) circuit, as shown in Figure 3. This device has been designed for optimum performance in this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer to better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.

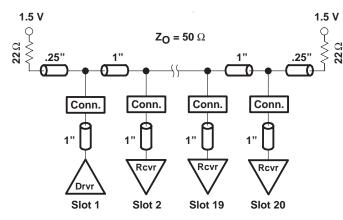


Figure 2. High-Drive Test Backplane

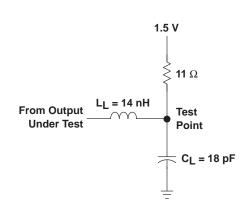


Figure 3. High-Drive RLC Network



SN74GTLP2033 8-BIT LVTTL-TO-GTLP ADJUSTABLE-EDGE-RATE REGISTERED TRANSCEIVER WITH SPLIT LVTTL PORT AND FEEDBACK PATH SCES352C - JUNE 2001 - REVISED SEPTEMBER 2001

switching characteristics over recommended operating conditions for the bus transceiver function (unless otherwise noted) (see Figure 3)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	EDGE RATE [†]	TYP‡	UNIT
^t PLH	AI		0	4.7	
tPHL	(buffer)	В	Slow	5	ns
^t PLH	AI	D	Fact	3.7	
tPHL	(buffer)	В	Fast	4	ns
^t PLH	LEAB	D	Claur	5.5	20
^t PHL	(latch mode)	В	Slow	5.8	ns
^t PLH	LEAB	В	Fact	4.6	ns
^t PHL	(latch mode)	В	Fast	4.8	115
^t PLH	CLKAB	В	Slow	5.8	20
^t PHL	(flip-flop mode)	D	SIOW	6	ns
^t PLH	CLKAB	В	Fast	4.9	ns
^t PHL	(flip-flop mode)	D	Fasi	4.9	115
^t PLH	OMODE	В	Slow	5.5	
^t PHL		D	SIOW	5.7	ns
^t PLH	OMODE	В	Fast	4.5	20
^t PHL	OIVIODE	D	Γαδι	4.7	ns
	Rise time, B-port outputs (20	9/ to 909/)	Slow	1.8	20
t _r		70 10 0070)	Fast	1.1	ns
+.	Fall time, B-port outputs (80%	// to 20%/)	Slow	3.4	20
t _f		/0 10 20 /0)	Fast	2.6	ns

[†]Slow (ERC = H) and Fast (ERC = L)

[‡] All typical values are at V_{CC} = 3.3 V, T_A = 25°C. All values are derived from TI-SPICE models.





24-Apr-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
SN74GTLP2033DGGR	ACTIVE	TSSOP	DGG	48	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	GTLP2033	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com

PACKAGE OPTION ADDENDUM

24-Apr-2015

PACKAGE MATERIALS INFORMATION

www.ti.com

TAPE AND REEL INFORMATION

REEL DIMENSIONS

TEXAS INSTRUMENTS





TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74GTLP2033DGGR	TSSOP	DGG	48	2000	330.0	24.4	8.6	15.8	1.8	12.0	24.0	Q1
SN74GTLP2033ZQLR	BGA MI CROSTA R JUNI OR	ZQL	56	1000	330.0	16.4	4.8	7.3	1.45	8.0	16.0	Q1

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

14-Jul-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74GTLP2033DGGR	TSSOP	DGG	48	2000	367.0	367.0	45.0
SN74GTLP2033ZQLR	BGA MICROSTAR JUNIOR	ZQL	56	1000	333.2	345.9	28.6

MECHANICAL DATA

MTSS003D - JANUARY 1995 - REVISED JANUARY 1998

DGG (R-PDSO-G**)

PLASTIC SMALL-OUTLINE PACKAGE

48 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold protrusion not to exceed 0,15.
- D. Falls within JEDEC MO-153



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products		Applications			
Audio	www.ti.com/audio	Automotive and Transportation	www.ti.com/automotive		
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications		
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers		
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps		
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy		
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial		
Interface	interface.ti.com	Medical	www.ti.com/medical		
Logic	logic.ti.com	Security	www.ti.com/security		
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense		
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video		
RFID	www.ti-rfid.com				
OMAP Applications Processors	www.ti.com/omap	TI E2E Community	e2e.ti.com		
Wireless Connectivity	www.ti.com/wirelessconnectivity				

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2016, Texas Instruments Incorporated